

General Description

The 100N04 uses advanced trench technology to provide excellent $R_{DS(on)}$. This device is suitable for PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

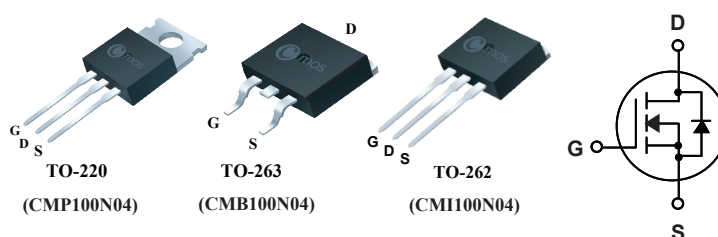
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
40V	4mΩ	100A

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

TO-220/263/262 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	100	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	56	A
I_{DM}	Pulsed Drain Current	400	A
EAS	Single Pulse Avalanche Energy ¹	800	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	260	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	54	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.48	°C/W

Electrical Characteristics (T_J=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =25A	---	3.3	4	mΩ
		V _{GS} =4.5V , I _D =20A	---	4.8	6	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	---	3	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V , V _{GS} =0V	---	---	1	uA
		V _{DS} =40V , V _{GS} =0V , TC=125°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V , I _D =20A	---	26	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2	---	Ω
Q _g	Total Gate Charge	I _D =30A	---	70	---	nC
Q _{gs}	Gate-Source Charge	V _{DD} =32V	---	21	---	
Q _{gd}	Gate-Drain Charge	V _{GS} =4.5V	---	36	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =20V	---	40	---	ns
T _r	Rise Time	I _D =40A	---	112	---	
T _{d(off)}	Turn-Off Delay Time	R _G =4.7Ω	---	144	---	
T _f	Fall Time	V _{GS} =10V	---	85	---	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	6500	---	pF
C _{oss}	Output Capacitance		---	470	---	
C _{rss}	Reverse Transfer Capacitance		---	420	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	100	A
I _{SM}	Pulsed Source Current		---	---	400	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =40A , T _J =25°C	---	---	1.2	V

Note :

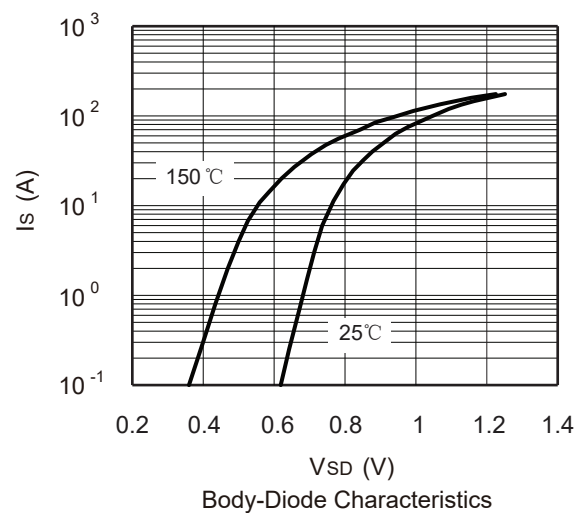
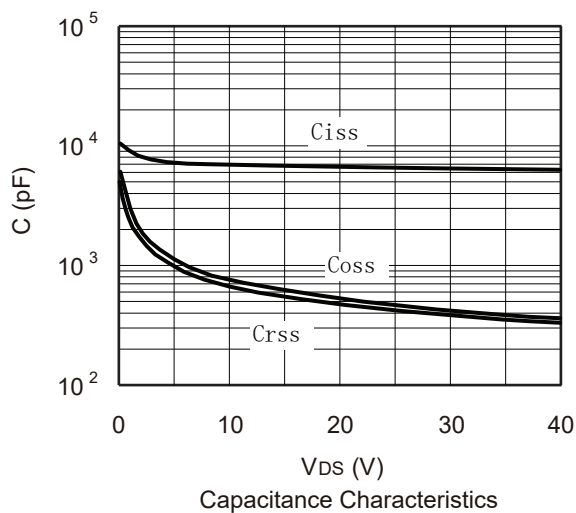
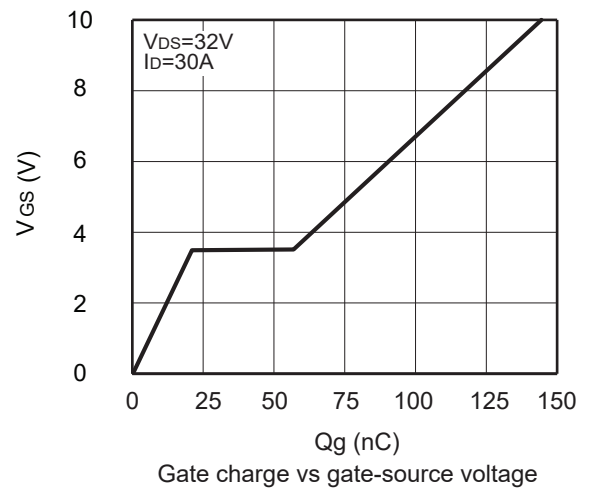
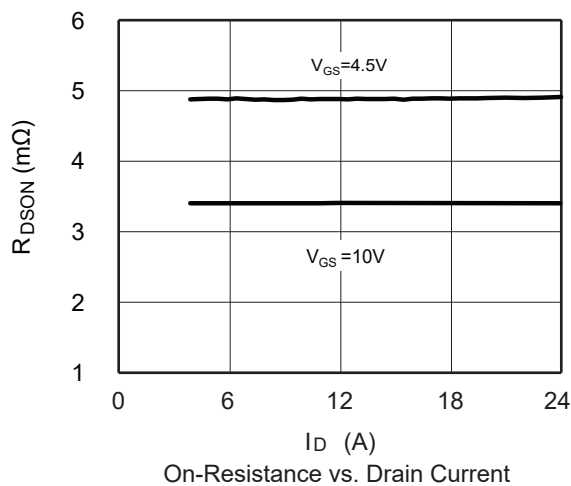
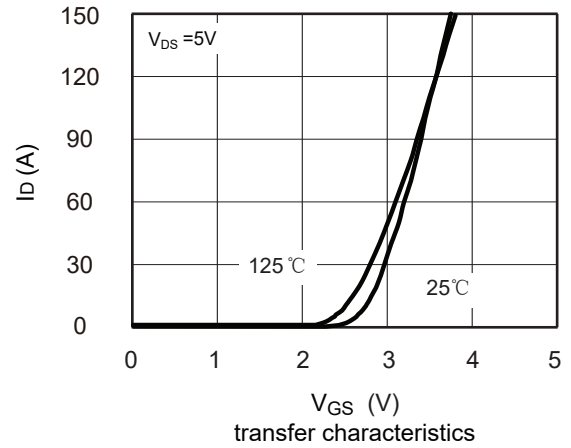
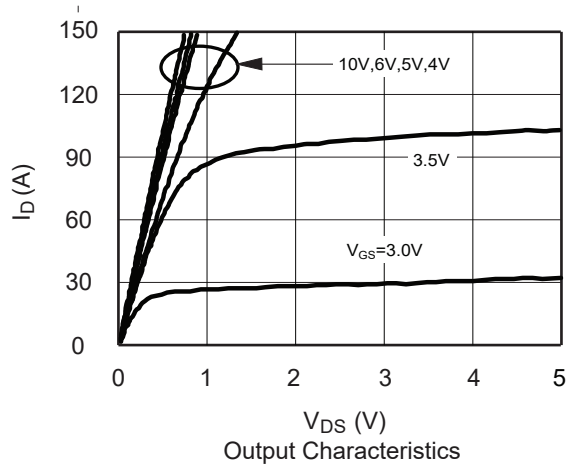
1.The EAS data shows Max. rating . The test condition is V_{DD}=35V , V_{GS}=10V , L=1mH , I_{AS}=40A.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

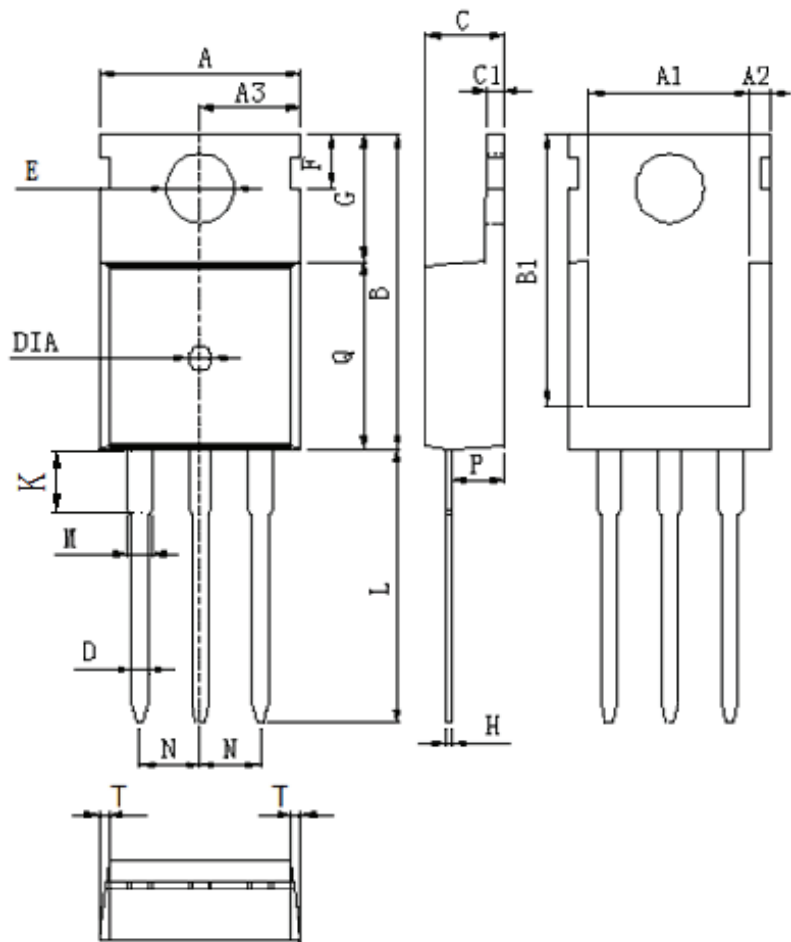
Typical Characteristics



Package Dimension

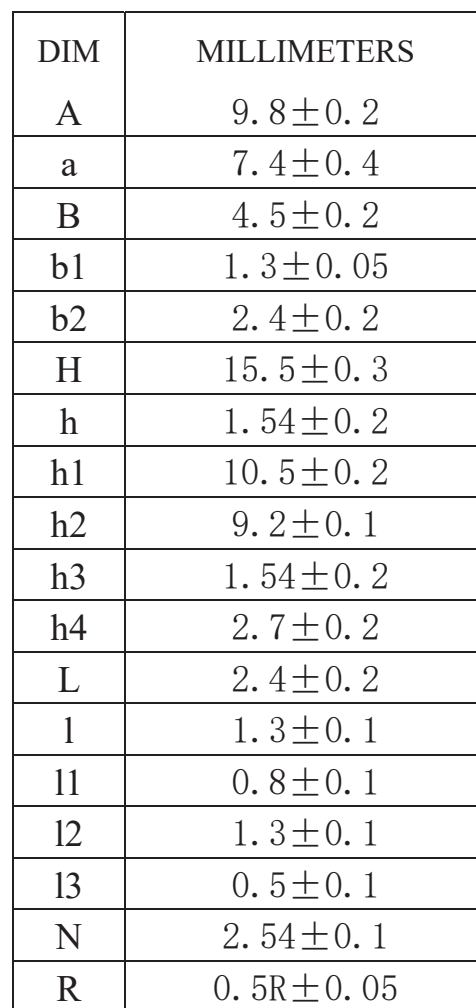
TO-220

Unit :mm



DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5 (deep 0.2)

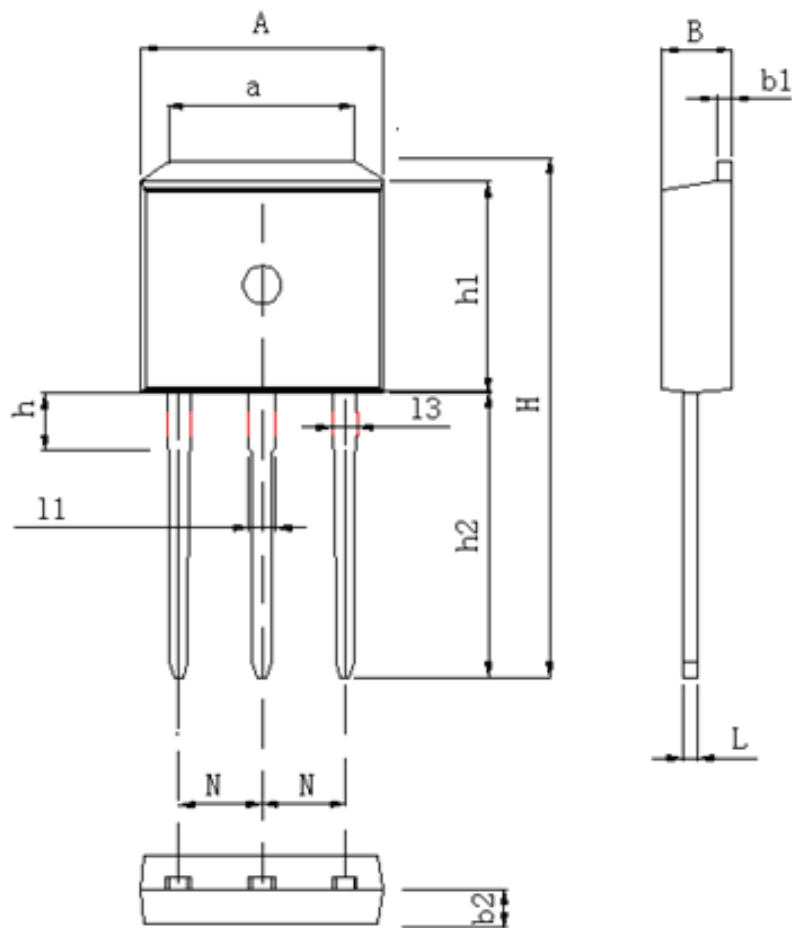
Unit :mm



Package Dimension

TO-262

Unit :mm



DIM	MILLIMETERS
A	9.98±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	23.9±0.3
h	3.1±0.2
h1	9.16±0.2
h2	13.2±0.2
L	0.5±0.1
11	1.3±0.1
12	0.8±0.1
N	2.45±0.1